

### Nch 800V 2A Power MOSFET

$V_{DSS}$	800V
R <sub>DS(on)</sub> (Max.)	$4.3\Omega$
I <sub>D</sub>	2A
$P_D$	36W

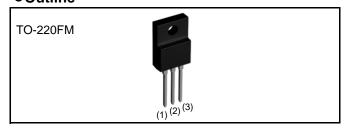
### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage ( $V_{GSS}$ ) guaranteed to be  $\pm 30V$ .
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

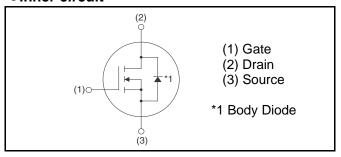
### Application

Switching Power Supply

#### Outline



#### ●Inner circuit



Packaging specifications

	Packaging	Bulk
T	Reel size (mm)	-
	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R8002ANX

### • Absolute maximum ratings( $T_a = 25^{\circ}C$ )

Paramete	Symbol	Value	Unit	
Drain - Source voltage		$V_{DSS}$	800	V
Continuous dusin surrent	T <sub>c</sub> = 25°C	I <sub>D</sub> *1	±2	А
Continuous drain current	T <sub>c</sub> = 100°C	I <sub>D</sub> *1	±1	А
Pulsed drain current	•	I <sub>D,pulse</sub> *2	±8	А
Gate - Source voltage		$V_{GSS}$	±30	V
Avalanche energy, single pulse		E <sub>AS</sub> *3	0.265	mJ
Avalanche energy, repetitive		E <sub>AR</sub> *4	0.212	mJ
Avalanche current		I <sub>AR</sub> *3	1	А
Power dissipation (T <sub>c</sub> = 25°C)		$P_{D}$	36	W
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C
Reverse diode dv/dt		dv/dt *5	15	V/ns

# • Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 2A$ $T_{j} = 125^{\circ}C$	50	V/ns

### ●Thermal resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	UTIIL
Thermal resistance, junction - case	$R_{thJC}$	-	ı	3.41	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	70	°C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	1	265	°C

# •Electrical characteristics( $T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	800	-	1	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V$ , $I_D = 2A$	-	900	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS}$ = 800V, $V_{GS}$ = 0V $T_j$ = 25°C $T_j$ = 125°C	-	0.1	100 1000	μΑ
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = 10V$ , $I_D = 1mA$	3	-	5	V
Static drain - source on - state resistance	R <sub>DS(on)</sub> *6	$V_{GS} = 10V$ , $I_D = 1A$ $T_j = 25$ °C $T_j = 125$ °C	-	3.3 6.63	4.3	Ω
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	5.9	-	Ω

# ●Electrical characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g <sub>fs</sub> *6	$V_{DS} = 10V, I_{D} = 1.0A$	0.5	1	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	210	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	130	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	14	-	
Effective output capacitance, energy related	$C_{\text{o(er)}}$	$V_{GS} = 0V$ ,	-	15.5	1	٦,
Effective output capacitance, time related	$C_{o(tr)}$	$V_{DS} = 0V \text{ to } 480V$	-	15.6	-	pF
Turn - on delay time	t <sub>d(on)</sub> *6	$V_{DD} \simeq 400V$ , $V_{GS} = 10V$	-	17	-	
Rise time	t <sub>r</sub> *6	I <sub>D</sub> = 1A	-	20	-	no
Turn - off delay time	t <sub>d(off)</sub> *6	$R_L = 400\Omega$	-	33	66	ns
Fall time	t <sub>f</sub> *6	$R_G = 10\Omega$	-	70	140	

# ● Gate Charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymphol	Conditions	Values			l lm:4
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Qg *6	V <sub>DD</sub> ≃ 400V	-	12.7	ı	
Gate - Source charge	Q <sub>gs</sub> *6	I <sub>D</sub> = 2A	-	2.7	1	nC
Gate - Drain charge	Q <sub>gd</sub> *6	V <sub>GS</sub> = 10V	-	4.3	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq 400V$ , $I_D = 2A$	-	7.4	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*3</sup> L  $^{\simeq}$  500 $\mu$ H,  $V_{DD}$  = 50V,  $R_{G}$  = 25 $\Omega$ , starting  $T_{j}$  = 25°C

<sup>\*4</sup> L  $^{\sim}$  500 $\mu$ H, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , starting T<sub>j</sub> = 25°C, f = 10kHz

<sup>\*5</sup> Reference measurement circuits Fig.5-1.

<sup>\*6</sup> Pulsed

# ●Body diode electrical characteristics (Source-Drain)(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	I <sub>S</sub> *1	T <sub>c</sub> = 25°C	-	,	2	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2	*2	-	-	8	А
Forward voltage	V <sub>SD</sub> *6	$V_{GS} = 0V$ , $I_S = 2A$	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub> *6		-	481	-	ns
Reverse recovery charge	Q <sub>rr</sub> *6	I <sub>S</sub> = 2A di/dt = 100A/us	-	2.5	-	μС
Peak reverse recovery current	I <sub>rrm</sub> *6		-	10.5	-	Α
Peak rate of fall of reverse recovery current	di <sub>rr</sub> /dt	T <sub>j</sub> = 25°C	-	50	-	A/μs

### ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	0.486	
R <sub>th2</sub>	1.31	K/W
R <sub>th3</sub>	1.96	

Symbol	Value	Unit
C <sub>th1</sub>	0.00095	
C <sub>th2</sub>	0.0112	Ws/K
C <sub>th3</sub>	0.521	

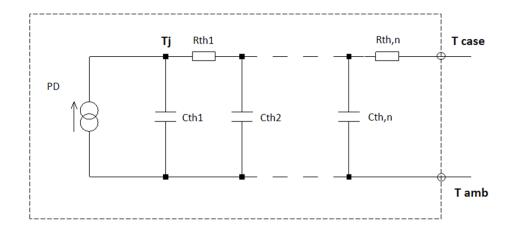
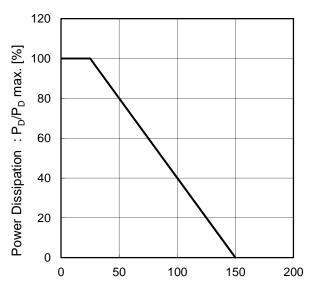
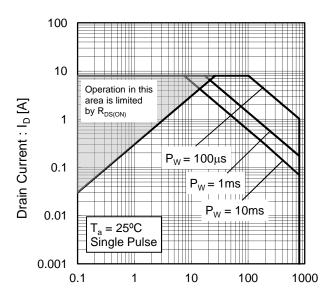


Fig.1 Power Dissipation Derating Curve



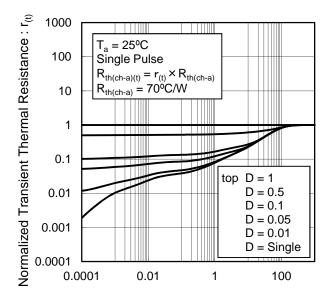
Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width : P<sub>W</sub> [s]

Fig.4 Avalanche Current vs Inductive Load

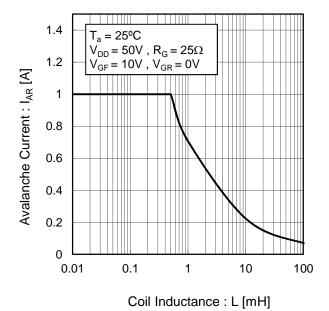
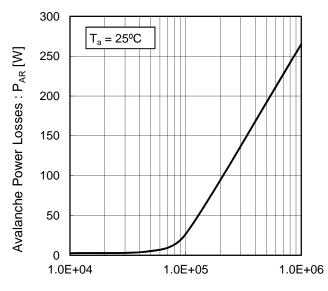


Fig.5 Avalanche Power Losses



Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs Junction Temperature

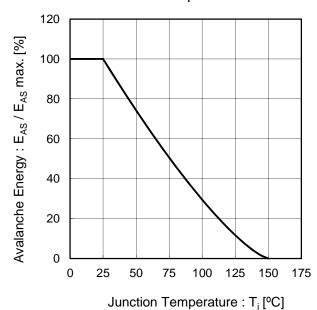


Fig.7 Typical Output Characteristics(I)

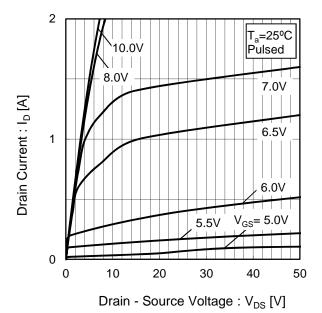


Fig.8 Typical Output Characteristics(II)

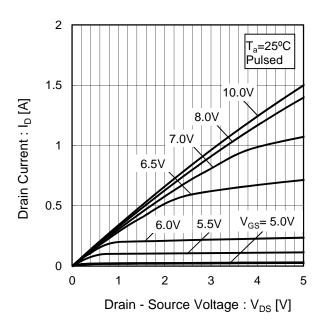


Fig.9  $T_j$  = 150°C Typical Output Characteristics(I)

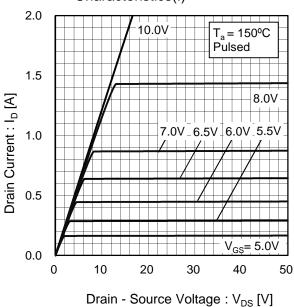
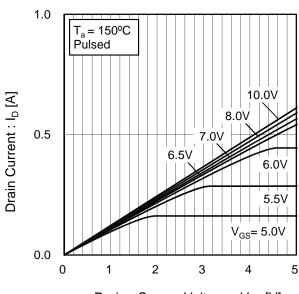
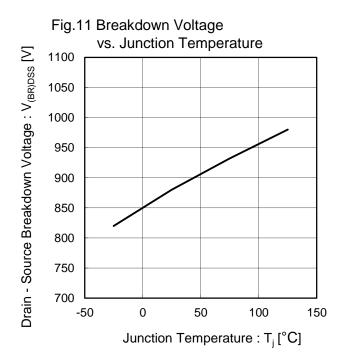


Fig.10 T<sub>j</sub> = 150°C Typical Output Characteristics(II)





 $\begin{array}{c} 10 \\ V_{DS} = 10V \\ Pulsed \\ \hline 1 \\ T_a = 125^{\circ}C \\ T_a = 75^{\circ}C \\ T_a = 25^{\circ}C \\ T_a = -25^{\circ}C \\ \end{array}$ 

Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.12 Typical Transfer Characteristics

Fig.13 Gate Threshold Voltage
vs. Junction Temperature

6

VDS=10V
ID=1mA
Pulsed
Pulsed

3

Junction Temperature : T<sub>i</sub> [°C]

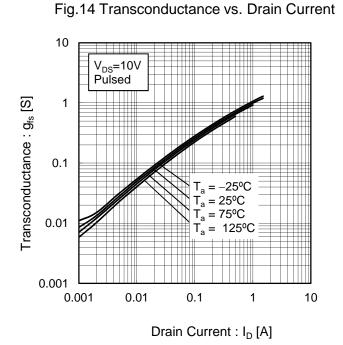


Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage 10 T<sub>a</sub>=25°C Static Drain - Source On-State Resistance Pulsed 8 6  $I_{D} = 2.0A$  $: R_{\mathsf{DS}(\mathsf{on})} \left[ \Omega \right]$  $I_{D} = 1.0A$ 4 2 0 0 10 20 30 Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature 9 V<sub>DS</sub> = 10V Pulsed Static Drain - Source On-State Resistance 8 7 6 I<sub>D</sub>=2A 5  $: R_{\mathsf{DS}(\mathsf{on})} \left[ \Omega \right]$ 4  $I_D=1A$ 3 2 1 0 -50 0 50 100 150

Junction Temperature : T<sub>i</sub> [°C]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

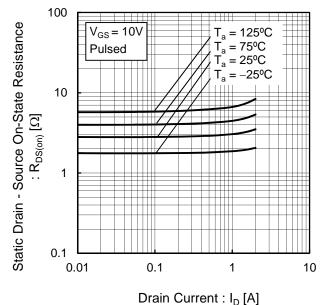
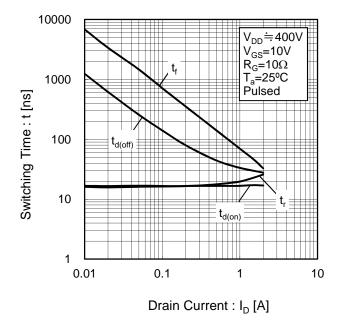


Fig.18 Typical Capacitance vs. Drain - Source Voltage 10000 T<sub>a</sub>=25°C f=1MHz V<sub>GS</sub>=0V 1000 Capacitance: C [pF]  $C_{iss}$ 100 10  $\mathsf{C}_{\mathsf{rss}}$ 0.01 0.1 10 100 1000 Drain - Source Voltage :  $V_{DS}[V]$ 

Fig.19 Coss Stored Energy

Fig.20 Switching Characteristics

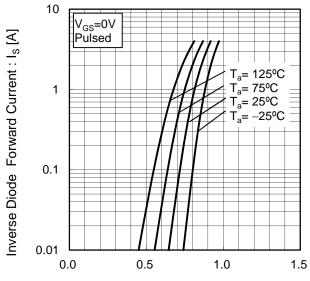


12 T<sub>a</sub>=25°C ∨<sub>DD</sub>=400V 10 I<sub>D</sub>=2A Pulsed Gate - Source Voltage: V<sub>GS</sub> [V] 8 6 4 2 0 0 5 10 15 20

Drain - Source Voltage : V<sub>DS</sub> [V]

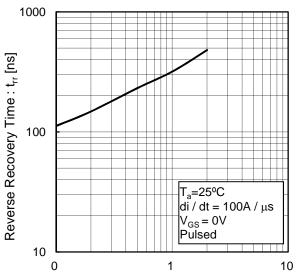
Total Gate Charge : Qq [nC]

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

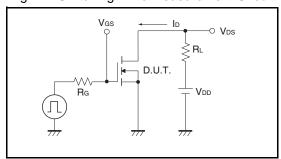


Fig.2-1 Gate Charge Measurement Circuit

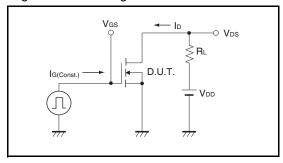


Fig.3-1 Avalanche Measurement Circuit

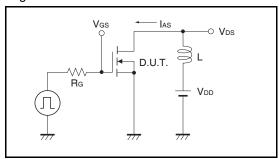


Fig.4-1 dv/dt Measurement Circuit

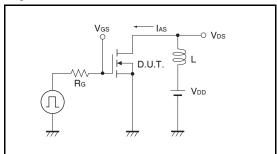


Fig.5-1 di/dt Measurement Circuit

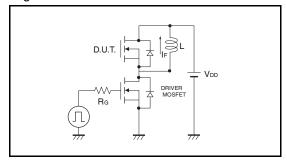


Fig.1-2 Switching Waveforms

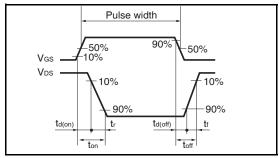


Fig.2-2 Gate Charge Waveform

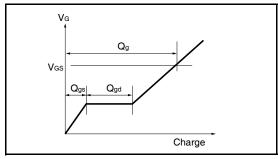


Fig.3-2 Avalanche Waveform

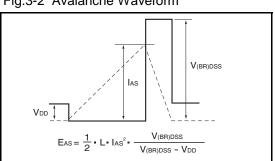


Fig.4-2 dv/dt Waveform

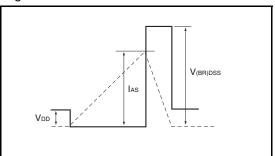
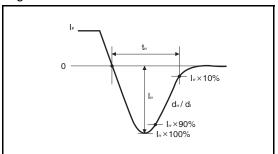
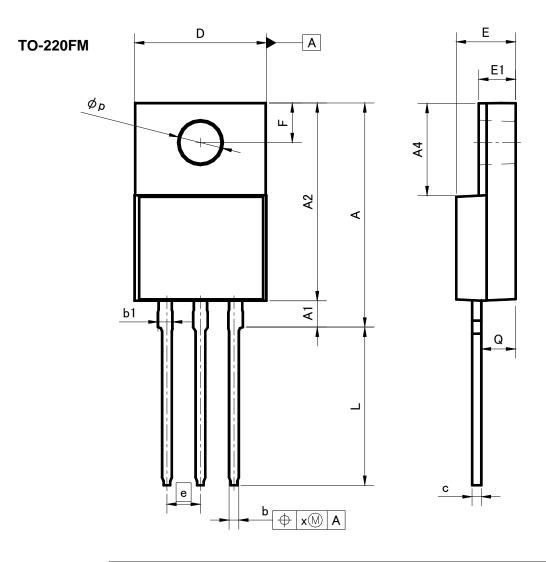


Fig.5-2 di/dt Waveform



# ●Dimensions (Unit : mm)



DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
E	4.40	4.80	0.173	0.189
е	2.54		0.	10
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
х	_	0.381	_	0.015

Dimension in mm/inches

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JÁPAN	USA	EU	CHINA
CLASSⅢ	CLASSII	CLASS II b	CLASSIII
CLASSIV		CLASSⅢ	

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  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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